描述 / Descriptions

PDFN5×6 封装 N 沟道场效应管。
N-Channel MOSFET in a PDFN5×6 Plastic Package .

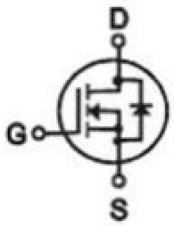
特征 / Features

低电阻可最大地降低导电损耗，低栅极电荷，可实现快速切换，低热阻，无卤产品。
Low $R_{DS(ON)}$ to minimize conductive loss, low Gate Charge for fast switching, Low Thermal resistance, HF Product.

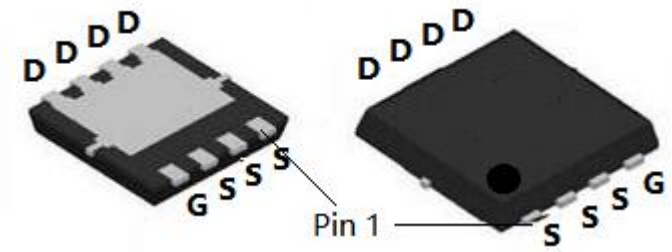
用途 / Applications

电池管理，MB/NB/UMPC/VGA 高频负载点同步 Buck 变换器，联网直流-直流电力系统，负荷开关。
Battery Management, High Frequency Point-of-Load Synchronous Buck Conventer for MB/NB/UMPC/VGA, Networking DC-DC Power System, Load Switch.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1、2、3： S　　PIN4：G　　PIN5、6、7、8：D

Pin	极性
1	S
2	S
3	S
4	G
5	D
6	D
7	D
8	D

放大及印章代码 / h_{FE} Classifications & Marking

见印章说明。See Marking Instructions.

极限参数 / Absolute Maximum Ratings(T_a=25℃)

参数 Parameter		符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage		V_{DS}	30	V
Drain Current - Continuous		I_D	146	A
Drain Current – Pulsed		I_{DM}	300	A
Gate-Source Voltage		V_{GS}	±20	V
Power Dissipation		P_D(T_c=25℃)	57	W
Single Pulse Avalanche Energy(L=0.5mH)		E_{AS}	315	mJ
Avalanche Current(L=0.5mH)		I_{AS}	30	A
Junction and Storage Temperature Range		T_j, T_{stg}	-55 to 150	℃
Thermal resistance, junction - ambient	t ≤ 10s	$R_{\theta JA}$	20	℃/ W
	Steady-State		50	
Thermal resistance, junction - case	Steady-State	$R_{\theta JC}$	2.2	

电性能参数 / Electrical Characteristics(Ta=25℃)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=250uA, V_{GS}=0V	30	35		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V			1.0	uA
Gate-Body leakage current	I_{GSS}	V_{DS}=0V, V_{GS}= ±20V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1	1.6	3	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=24A		1.5	1.8	mΩ
		V_{GS}=4.5V, I_D=12A		2.0	2.8	
Diode Forward Voltage	V_{SD}	I_S=1A, V_{GS}=0V		0.68	1	V
Input Capacitance	C_{iss}	V_{DS}=25V V_{GS}=0V f=1.0MHz		8500		pF
Output Capacitance	C_{oss}			890		
Reverse Transfer Capacitance	C_{rss}			670		
Gate resistance	R_g	V_{GS}=0V V_{DS}=0V f=1MHz		1.8		Ω
Total Gate Charge	$Q_{g(10V)}$	V_{GS}=10V, V_{DS}=15V, I_D=20A		60		nC
Total Gate Charge	$Q_{g(4.5V)}$			28		
Gate Source Charge	Q_{gs}			12		
Gate Drain Charge	Q_{gd}			9.5		

电性能参数 / Electrical Characteristics(Ta=25℃)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=10V V_{DS}=15V R_L=0.75Ω R_{GEN}=3Ω		12.5		ns
Turn-On Rise Time	t_r			6.0		
Turn-Off Delay Time	$t_{d(off)}$			47		
Turn-Off Fall Time	t_f			10.5		

电参数曲线图 / Electrical Characteristic Curve

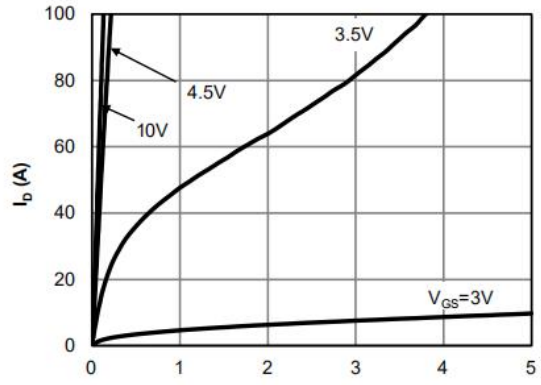


Figure 1: On-Region Characteristics

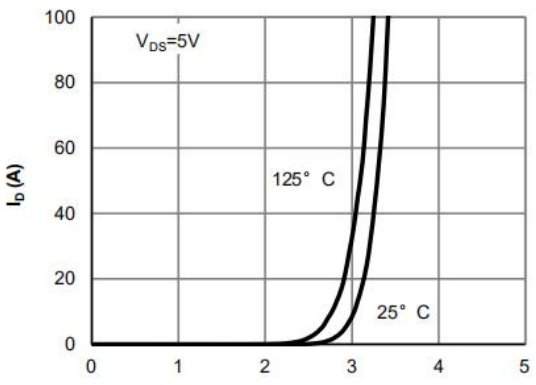


Figure 2: Transfer Characteristics

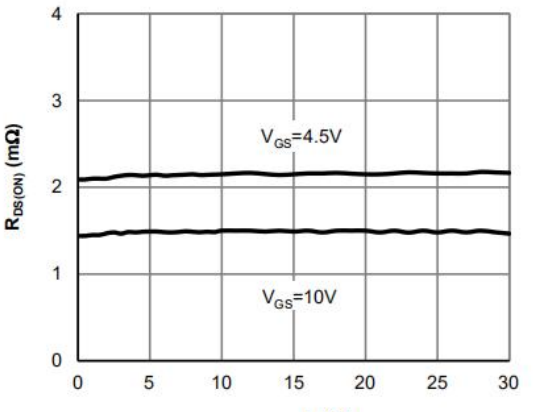


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

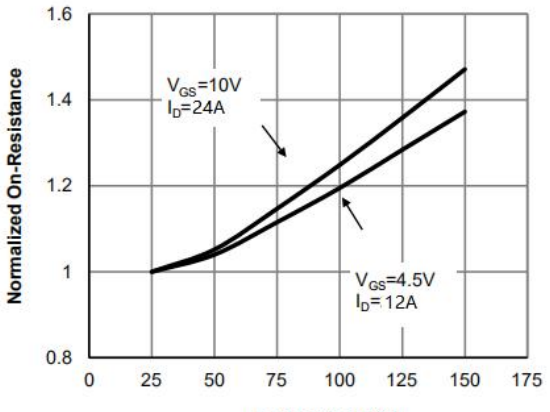


Figure 4: On-Resistance vs. Junction Temperature

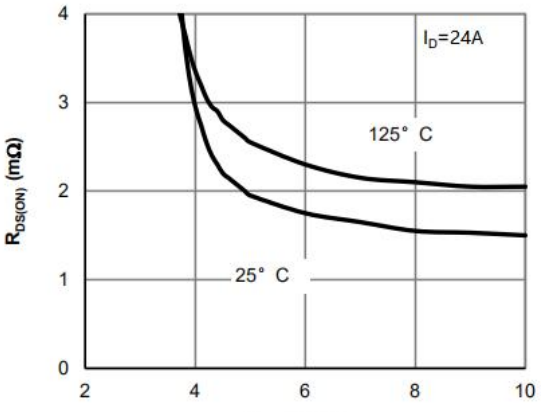


Figure 5: On-Resistance vs. Gate-Source Voltage

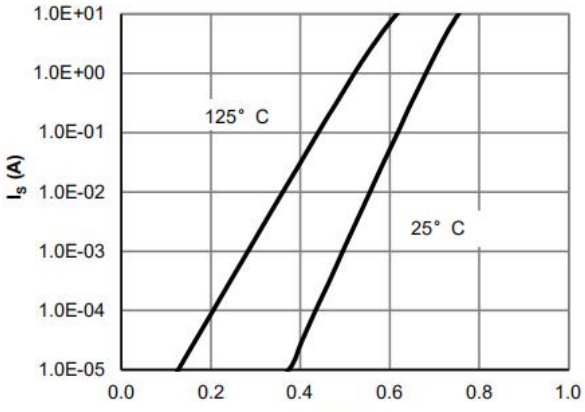


Figure 6: Body-Diode Characteristics

电参数曲线图 / Electrical Characteristic Curve

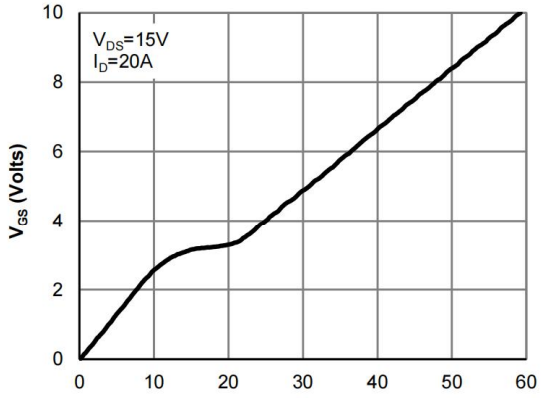


Figure 7: Gate-Charge Characteristics

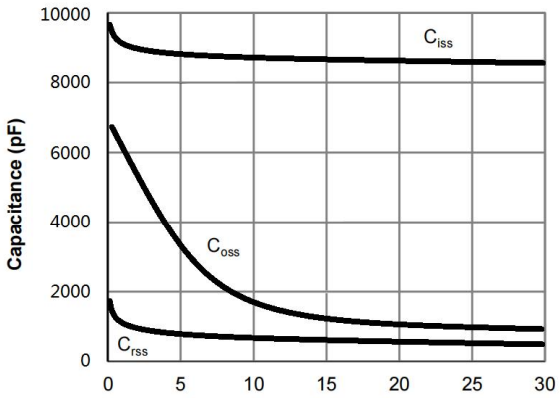
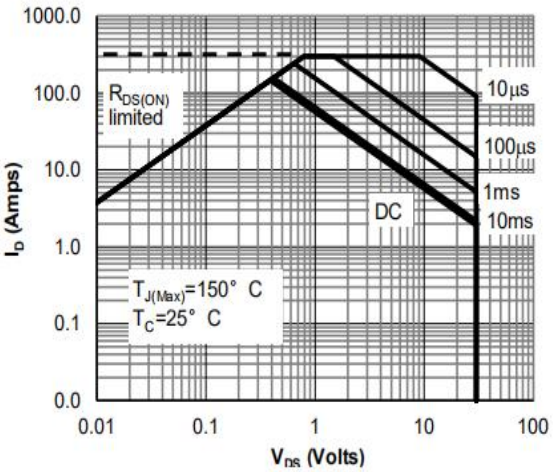


Figure 8: Capacitance Characteristics



V_{GS}> or equal to 4.5V
Figure 9: Maximum Forward Biased Safe Operating Area

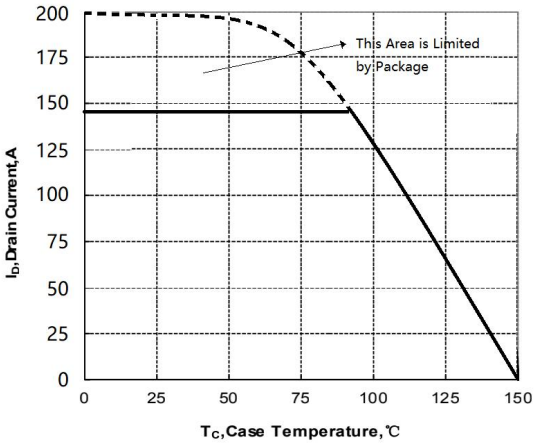


Figure 10. Maximum Continuous Drain Current vs Case Temperature

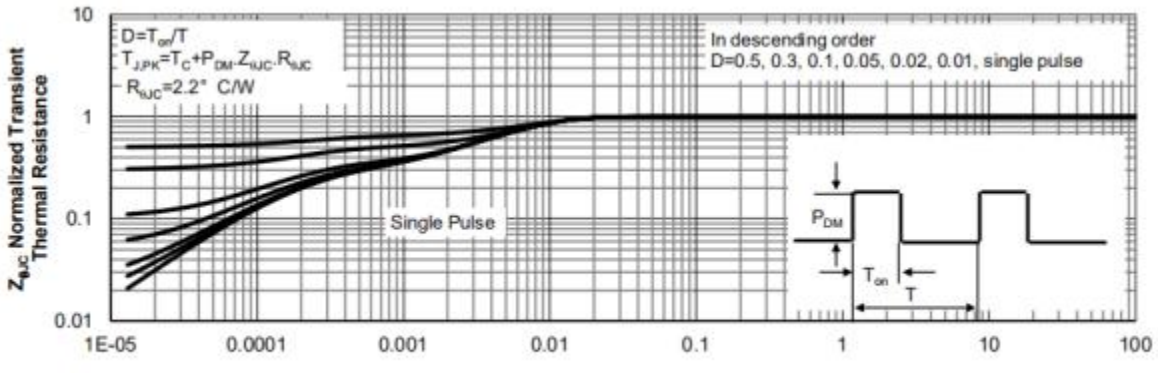
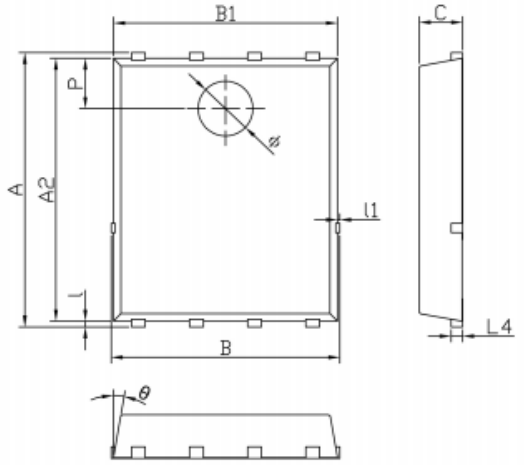


Figure 11 : Normalized Maximum Transient Thermal Impedance

外形尺寸图 / Package Dimensions

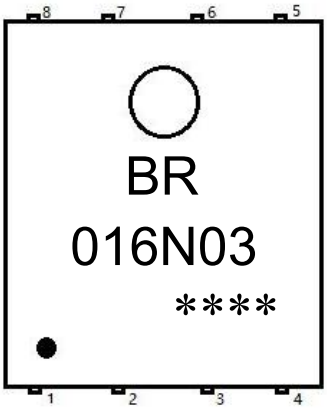
PDFN5 X6 Unit:mm



Dimensions In Millimeterer			
Symbol	MIN	TYP	MAX
A	5.90	6.00	6.10
a	3.91	4.01	4.11
A2	5.70	5.75	5.80
B	4.90	5.00	5.10
b	3.37	3.47	3.57
B1	4.80	4.90	5.00
C	0.90	0.95	1.00
L	0.35	0.40	0.45
l	0.06	0.13	0.20
L1	1.10	-	-
l1	-	-	0.10
L2	1.17	1.27	1.37
L4	0.21	0.26	0.34
L6	0.51	0.61	0.71
L7	0.51	0.61	0.71
P	1.00	1.10	1.20
θ	8°	10°	12°
Φ	1.10	1.20	1.30

Rev.00 201812

印章说明 / Marking Instructions



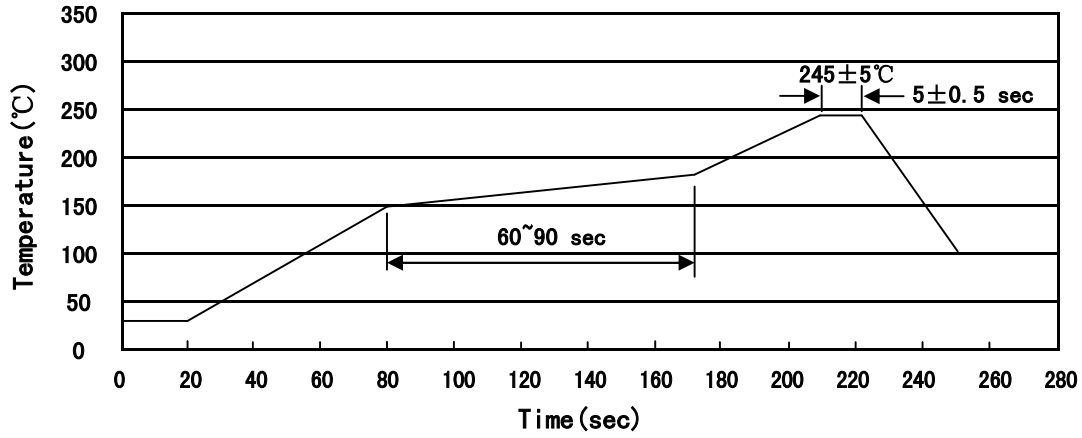
说明：

BR：	为公司代码
016N03：	为型号代码
****：	为生产批号代码，随生产批号变化

Note:

BR:	Company Code.
016N03:	Product Type Code.
****:	Lot No. Code, code change with Lot No.

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

1、预热温度 150～180℃，时间 60～90sec;

2、峰值温度 245±5℃，时间持续为 5±0.5sec;

3、焊接制程冷却速度为 2～10℃/sec.

Note:

1.Preheating:150~180℃, Time:60~90sec.

2.Peak Temp.:245±5℃, Duration:5±0.5sec.

3. Cooling Speed: 2~10℃/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5℃ 时间：10±1 sec. Temp.:260±5℃ Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
PDFN5×6	5000	2	10000	6	60000	13" × 12	360 × 360 × 50	380 × 335 × 366

使用说明 / Notices

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